

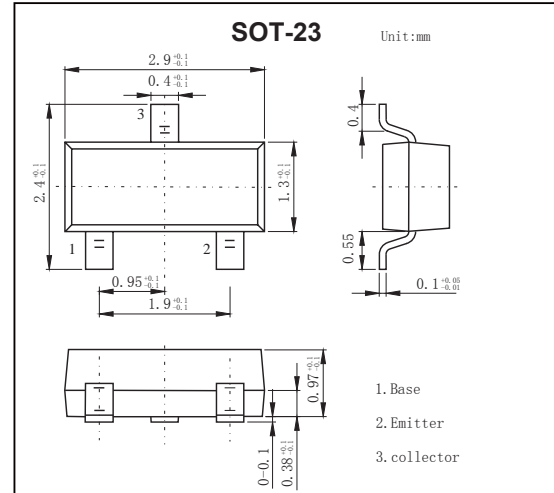
SOT-23 Plastic-Encapsulate Transistors

FEATURES

- Complementary to 2SC1623
- High voltage and high current
V_{CEO} = -50V (min.), I_C = -150mA (max.)
- Low noise: NF = 1dB (Typ.) at f = 1KHz
- PNP TRANSISTORS
- Collector-Base Voltage: V_{CB0} = -60V

MECHANICAL DATA

- Case style: SOT-23 molded plastic
- Mounting position: any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	-50	V
Collector-Emitter Voltage	V _{CEO}	-50	V
Emitter-Base Voltage	V _{EB0}	-5	V
Collector Current -Continuous	I _C	-150	mA
Collector Power Dissipation	P _C	200	mW
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55 to 150	°C

PACKAGE INFORMATION

Device	Package	Shipping
2SA1015	SOT-23	3000/Tape&Reel

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{CB0}	I _C = -100 μA, I _E = 0	-50			V
Collector-emitter breakdown voltage	V _{CEO}	I _C = -0.1mA, I _B = 0	-50			V
Emitter-base breakdown voltage	V _{EB0}	I _E = -100 μA, I _C = 0	-5			V
Collector cut-off current	I _{CB0}	V _{CB} = -50V, I _E = 0			-0.1	μA
Collector cut-off current	I _{CEO}	V _{CE} = -50V, I _B = 0			-0.1	μA
Emitter cut-off current	I _{EB0}	V _{EB} = -5V, I _C = 0			-0.1	μA
DC current gain	h _{FE}	V _{CE} = -6V, I _C = -2mA	130		400	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -100 mA, I _B = -10mA			-0.3	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = -100 mA, I _B = -10mA			-1.1	V
Transition frequency	f _T	V _{CE} = -10V, I _C = -1mA, f = 30MHz	80			MHz

h_{FE} Classification

Type	2SA1015-L	2SA1015-H
Range	130-200	200-400
Marking	BAL	BA